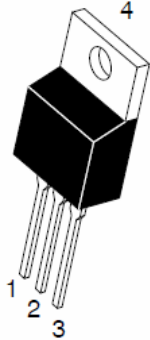
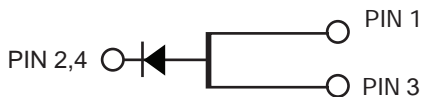


## Trench MOS Barrier Schottky Rectifier

**TO-220AB**  
**TSR10L100CT-S**



**ITO-220AB**  
**TSR10L100CTF-S**



### Features

- Advanced trench technology
- Low forward voltage drop
- Low power losses
- High efficiency operation
- Lead Free Finish, RoHS Compliant

### Applications

- DC/DC Converters
- AC/DC Adaptors
- Switching Power Supplies
- Freewheeling Diodes

### Maximum ratings and electrical characteristics (T<sub>J</sub> = 25°C unless otherwise noted)

Parameter		Symbol	Limit		Unit	
Maximum repetitive peak reverse voltage		VRRM	100		V	
Maximum average forward rectified current	per device	IF(AV)	10		A	
Peak forward surge current 8.3 ms single half sine- wave superimposed on rated load per diode		IFSM	160		A	
Operating junction and storage temperature range		TJ, TSTG	-55 to +150		°C	
Typical thermal resistance per leg		RθJC	TO-220AB		2	°C/W
			ITO-220AB		4	°C/W
Instantaneous forward voltage per diode			TYP.	MAX.	V	
	IF=2A	TJ=25°C	0.44	0.50		
	IF=2A	TJ=125°C	0.39	-		
	IF= 0A	TJ=25°C	0.63	0.70		
Instantaneous reverse current per diode at rated reverse voltage			-	50	µA	
			-	0	mA	

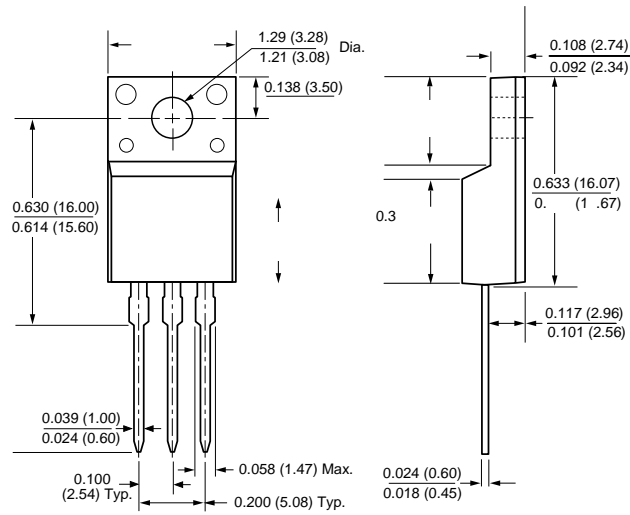
Notes:

(1) Pulse test: 300 µs pulse width, 1 % duty cycle

(2) Pulse test: Pulse width ≦ 40 ms



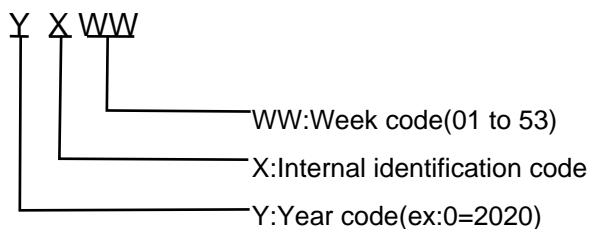
# PACKAGE OUTLINE DIMENSIONS



## Marking Information

- ①W : Company's trademark
- ②Product model : TSR L10 CT or TSR L10 CTF

### ③PDC information



## Packaging Information

1. Tube Dimensions

2. Inside Box

3. Outside Box

## Packaging Information

NO	UNIT	Tube Dimensions		Inside Box	Outside Box
		A	B		
Size	mm				